

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A stack-type semiconductor device formed by stacking a plurality of semiconductor devices, at least an undermost semiconductor device among the plurality of semiconductor devices comprising:

a semiconductor element having ~~a first through hole~~ holes formed therein and a plurality of electrodes formed on a first surface of the semiconductor ~~element~~ element, ~~each of the electrodes having second through holes formed therein, the second through holes respectively connecting with the first through holes, the second through holes having inner wall surfaces;~~

an insulating film formed on a region including the inner wall surfaces of the second through holes, the insulating film having third through holes inside the second through holes, respectively;

a conductive layer which is electrically connected to the electrodes, and is provided from the first surface through ~~an inner wall~~ walls of the ~~first through hole~~ holes to a second surface of the semiconductor ~~element~~ element, which is opposite to the first surface; and

a plurality of connecting portions provided on the conductive layer so that a distance between two connecting portions among the plurality of connecting portions is different from a distance between at least two electrodes among the plurality of electrodes, on at least one of the first and second surfaces.

2. (Currently Amended) A stack-type semiconductor device formed by stacking a plurality of the semiconductor devices ~~adjacent semiconductor devices~~ devices, ~~among the~~

~~plurality of the semiconductor devices being electrically connected by the conductive layer,~~  
each of the semiconductor device devices comprising:

a semiconductor element having ~~a first through hole~~ holes formed therein and  
a plurality of electrodes formed on a first surface of the semiconductor ~~element;~~  
element, each of the electrodes having second through holes formed therein, the second  
through holes respectively connecting with the first through holes, the second through holes  
having inner wall surfaces;

an insulating film formed on a region including the inner wall surfaces of the  
second through holes, the insulating film having third through holes inside the second through  
holes, respectively;

a conductive layer which is electrically connected to the electrodes, and is  
provided from the first surface through ~~an inner wall walls~~ of the first through hole holes to a  
second surface of the semiconductor element which is opposite to the first surface; and

a plurality of connecting portions provided on the conductive layer so that a  
distance between two connecting portions among the plurality of connecting portions is  
different from a distance between at least two electrodes among the plurality of electrodes, on  
at least one of the first and second ~~surfaces~~ surfaces,

wherein adjacent semiconductor devices are electrically connected by the  
conductive layer to the plurality of the semiconductor devices.

3. (Canceled)

4. (Canceled)

5. (Currently Amended) The stack-type semiconductor device as defined in  
claim 1,

wherein ~~an the~~ the undermost semiconductor device is arranged so that the first  
surface of the semiconductor element faces other stacked semiconductor devices.